

N-channel 30 V 3.15 m $\Omega$  logic level MOSFET in LFPAK33 using NextPower Technology

Rev. 4 — 15 June 2012

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment

#### **1.2 Features and benefits**

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology

#### 1.3 Applications

- DC-to-DC converters
- Load switching

#### 1.4 Quick reference data

unction technology			
	-		

loads

Synchronous buck regulator

 Ultra low QG, QGD, & QOSS for high system efficiencies at low and high

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	$T_j = 25 \ ^{\circ}C$	-	-	30	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	<u>[1]</u> -	-	70	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	88	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
D0011	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	3.5	4.05	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	2.7	3.15	mΩ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.3	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $V_{DS}$ = 15 V; see Figure 12; see Figure 13	-	16.1	-	nC

[1] Continuous current is limited by package.

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		2
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		mbb076 S
			SOT1210 (LFPAK33)	

### 3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PSMN3R0-30MLC	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210		

### 4. Limiting values

#### Table 4. Limiting values

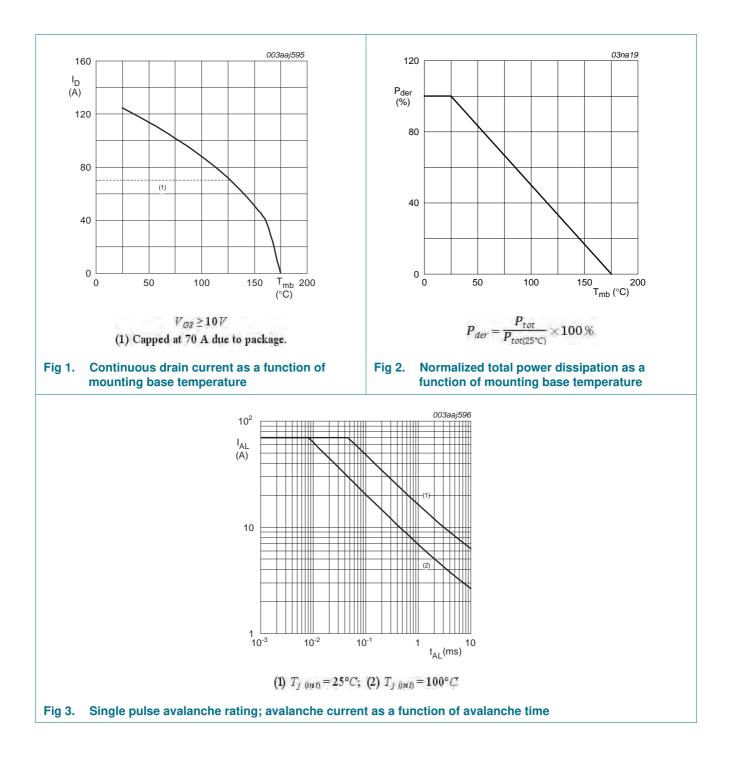
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	$T_j = 25 \ ^{\circ}C$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
ID	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	70	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	70	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <u>Figure 4</u>	-	498	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	88	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	350	-	V
Source-drain o	liode				
ls	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u> _	70	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	498	А
Avalanche rug	gedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 70 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 $\Omega$ ; unclamped; see Figure 3	-	64	mJ

[1] Continuous current is limited by package.

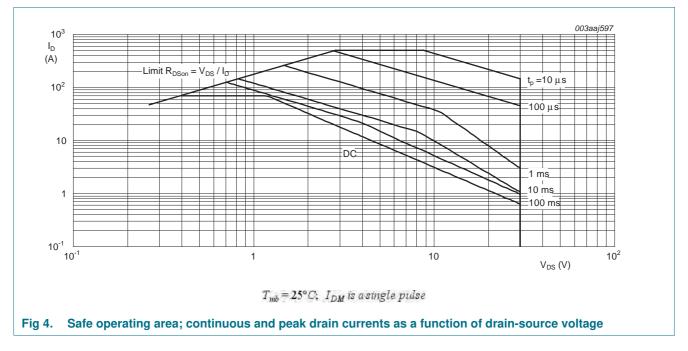
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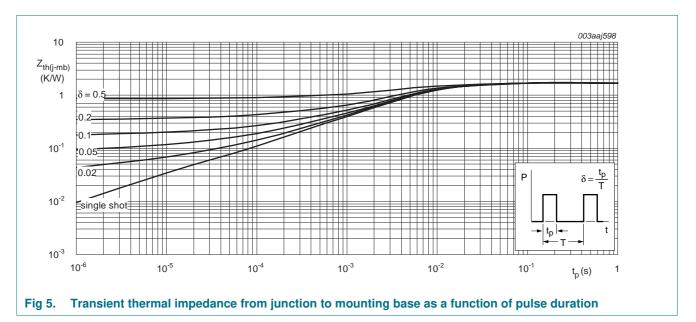
#### N-channel 30 V 3.15mΩ logic level MOSFET in LFPAK33 using NextPower Technology



### 5. Thermal characteristics

#### Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base see Figure 5		-	1.49	1.7	K/W



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Product data sheet

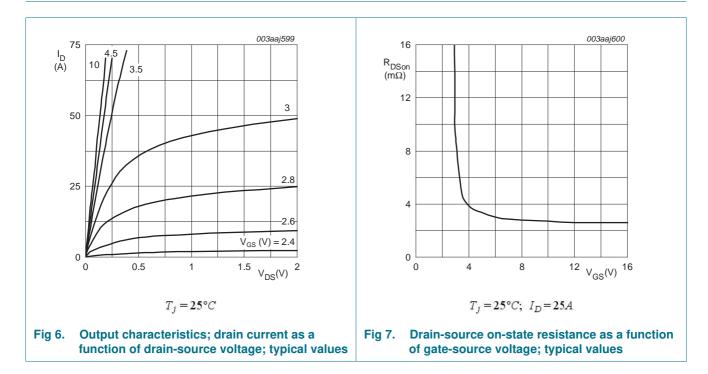
#### N-channel 30 V 3.15mΩ logic level MOSFET in LFPAK33 using NextPower Technology

### 6. Characteristics

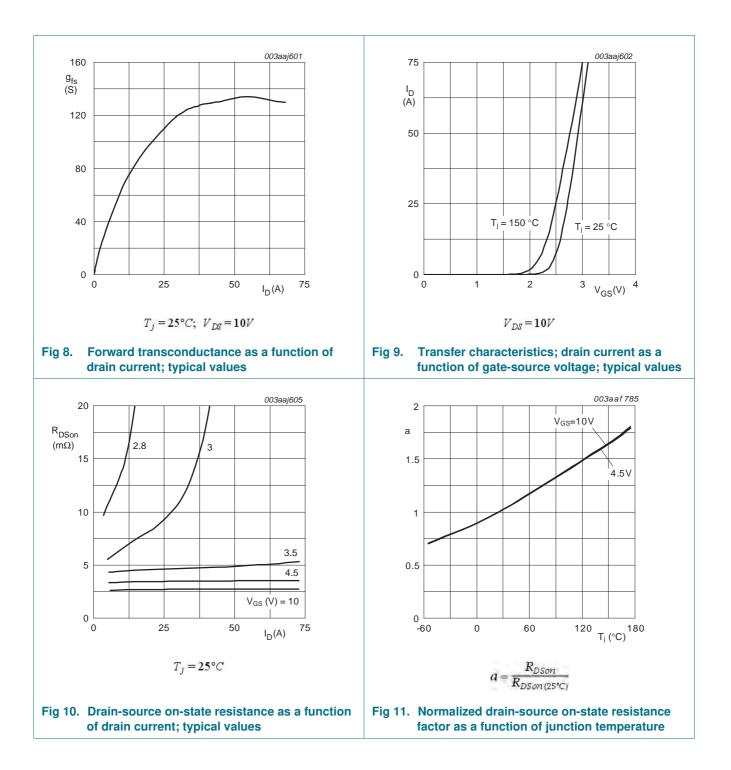
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_{D} = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}\text{C}$	30	-	-	V
	breakdown voltage	$I_{D} = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_{j} = -55 \ ^{\circ}\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.45	1.74	2.15	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature		-	-4	-	mV/K
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	3.5	4.05	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	6.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	2.7	3.15	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	5.35	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	0.37	0.74	1.48	Ω
Dynamic o	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	34.8	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	16.1	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	32.3	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	6.2	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	see Figure 12; see Figure 13	-	3.7	-	nC
$Q_{GS(\text{th-pl})}$	post-threshold gate-source charge		-	2.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	4.3	-	nC
$V_{GS(\text{pl})}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	2.9	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	2330	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	480	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	180	-	pF

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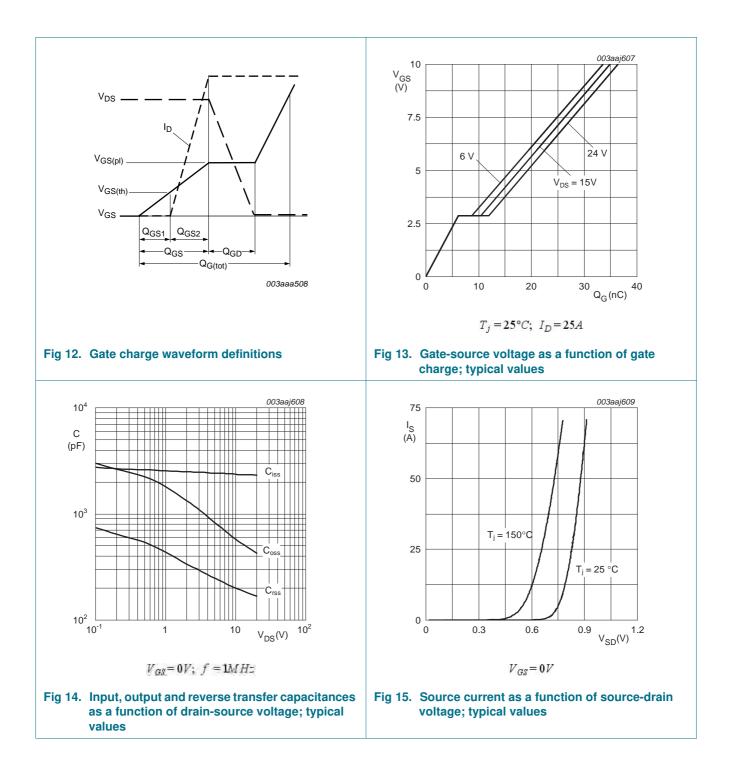
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_L$ = 0.6 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	16.2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	27.2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	18.3	-	ns
t <sub>f</sub>	fall time		-	13.7	-	ns
Q <sub>oss</sub>	output charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 0 \ V; \ V_{DS} = 15 \ V; \ f = 1 \ MHz; \\ T_j = 25 \ ^\circ C \end{array}$	-	14.2	-	nC
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	22.7	-	ns
Qr	recovered charge	V <sub>DS</sub> = 15 V	-	17	-	nC
t <sub>a</sub>	reverse recovery rise time	$\label{eq:VGS} \begin{array}{l} V_{GS} = 0 \ V; \ I_S = 25 \ A; \ dI_S/dt = -100 \ A/\mu s; \\ V_{DS} = 15 \ V; \ see \ \underline{Figure \ 16} \end{array}$	-	13.7	-	ns
t <sub>b</sub>	reverse recovery fall time		-	9	-	ns



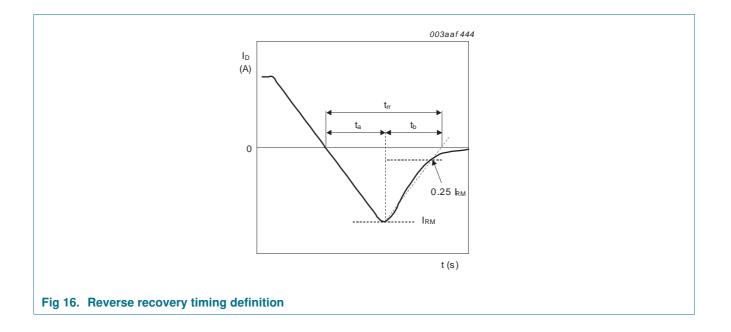
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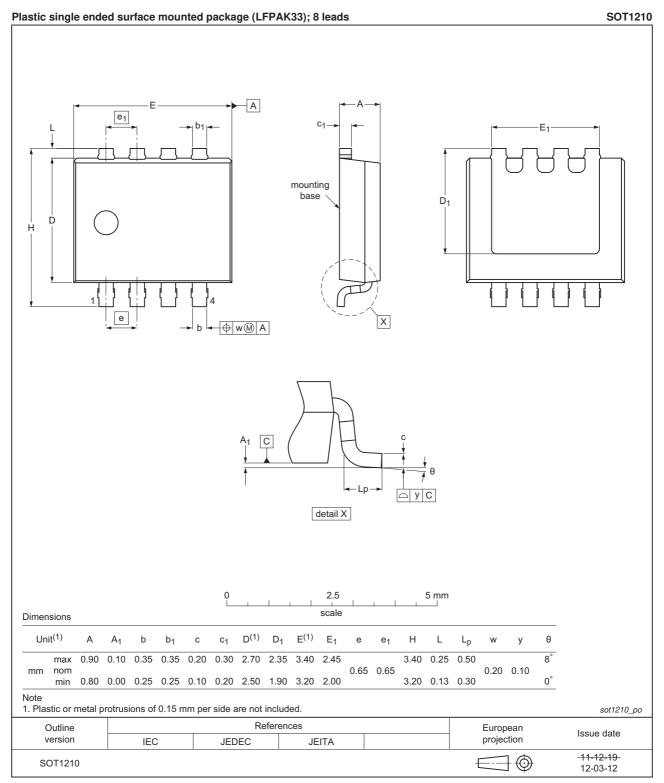


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### 7. Package outline



#### Fig 17. Package outline SOT1210 (LFPAK33)

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### 8. Revision history

#### Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R0-30MLC v.4	20120615	Product data sheet	-	PSMN3R0-30MLC v.3
Modifications:	<ul><li>Status changed fro</li><li>Various changes to</li></ul>	m objective to product.		
PSMN3R0-30MLC v.3	20120607	Objective data sheet	-	PSMN3R0-30MLC v.2

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### 9. Legal information

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Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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**Product data sheet** 

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